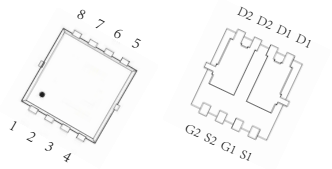
SZCJ

DFNWB3.3×3.3-8L-B Plastic-Encapsulate MOSFET

·Channel + P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)\ TYP}$	I_D
30V	10mΩ@10V	30A
	17mΩ@4.5V	
-30V	26mΩ@-10V	-20A
	40mΩ@-4.5V	

PDFNWB3.3×3.3-8L-B



DESCRIPTION

The CJAB2003 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

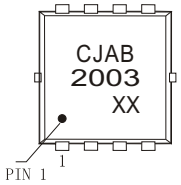
FEATURES

- Battery switch
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING

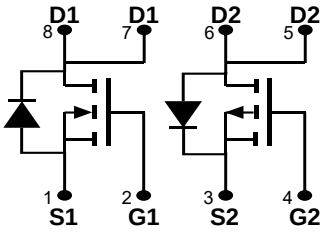


CJAB2003=Part No.

Solid dot=Pin1 indicator

XX=Date Code

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter		Symbol	Limit	Unit
N-MOSFET				
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	Ñ20	V
Continuous Drain Current		I_D ①	30	A
Pulsed Drain Current		I_{DM} ②	100	A
Single Pulsed Avalanche Energy		E_{AS} ③	80	mJ
P-MOSFET				
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	Ñ20	V
Continuous Drain Current		I_D ①	-20	A
Pulsed Drain Current		I_{DM} ②	-80	A
Single Pulsed Avalanche Energy		E_{AS} ④	45	mJ
Temperature and Thermal Resistance				
Thermal Resistance from Junction to Ambient	N-Ch	$R_{\theta JA}$ ⑦	83.3	℃/W
Thermal Resistance from Junction to Ambient	P-Ch	$R_{\theta JA}$ ⑦	83.3	℃/W
Thermal Resistance from Junction to Case	N-Ch	$R_{\theta JC}$ ①	4.17	℃/W
Thermal Resistance from Junction to Case	P-Ch	$R_{\theta JC}$ ①	5.0	℃/W
Power Dissipation	N-Ch	P_D ①	30	W
Power Dissipation	P-Ch	P_D ①	25	W
Operating Junction and Storage Temperature Range		T_J ,T_{stg}	-55~+150	℃

MOSFET ELECTRICAL CHARACTERISTICS

N-Channel MOSFET ELECTRICAL CHARACTERISTICS, T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D =250ÕA		30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =24V, V_{GS} =0V	T_J =25℃			1.0	ÕA
			T_J =125℃			100	
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =Ñ20V				Ñ100	nA
On characteristics ⑤							
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250ÕA		1.0	1.8	2.5	V
Static drain-source on-sate resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =8A			10	13	mÝ
		V_{GS} =4.5V, I_D =6A			17	22	mÝ
Dynamic characteristics ⑤⑥							
Input capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V, f =1MHz			1000		pF
Output capacitance	C_{oss}				143		
Reverse transfer capacitance	C_{rss}				130		
Gate resistance	R_g	f =1MHz			6.0		Ω
Switching characteristics ⑤⑥							
Total gate charge	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=8A			22		nC
Gate-source charge	Q_{gs}				2.8		
Gate-drain charge	Q_{gd}				5.2		
Turn-on delay time	$t_{d(on)}$	V_{DD}=15V, R_L=5q, V_{GS}=10V, R_{GEN}=10q			25		ns
Turn-on rise time	t_r				40		
Turn-off delay time	$t_{d(off)}$				140		
Turn-off fall time	t_f				80		
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V_{SD} ⑤	V_{GS} =0V, I_S=8A				1.2	V
Continuous drain-source diode forward current	I_S ①					30	A
Pulsed drain-source diode forward current	I_{SM} ②					100	A

MOSFET ELECTRICAL CHARACTERISTICS

P-Channel MOSFET ELECTRICAL CHARACTERISTICS, T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D = -250ÕA		-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V, V_{GS} =0V	T_J=25℃			-1.0	ÕA
			T_J=125℃			-100	
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =Ñ20V				Ñ100	nA
On characteristics ⑤							
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250ÕA		-1.0	-1.5	-2.5	V
Static drain-source on-sate resistance	$R_{DS(on)}$	V_{GS} =-10V, I_D =-8A			26	34	mÝ
		V_{GS} =-4.5V, I_D =-6A			40	52	
Dynamic characteristics ⑤⑥							
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V, f =1MHz			943		pF
Output capacitance	C_{oss}				107		
Reverse transfer capacitance	C_{rss}				90		
Gate resistance	R_g	f =1MHz			22		Ω
Switching characteristics ⑤⑥							
Total gate charge	Q_g	V_{GS}=-10V,V_{DS}=-15V, I_D=-8A			28		nC
Gate-source charge	Q_{gs}				3.2		
Gate-drain charge	Q_{gd}				8.5		
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V,R_L=5q, V_{GS}=-10V, R_{GEN}=10q			32		ns
Turn-on rise time	t_r				55		
Turn-off delay time	$t_{d(off)}$				150		
Turn-off fall time	t_f				60		
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V_{SD} ⑤	V_{GS} =0V, I_S=-5A				-1.2	V
Continuous drain-source diode forward current	I_S ①					-20	A
Pulsed drain-source diode forward current	I_{SM} ②					-80	A

Notes:

1.T_C=25℃ Limited only by maximum temperature allowed.

2.P_W≤10μs, Duty cycle≤1%.

3.EAS condition: VDD=15V,VGS=10V, L=0.5mH, Rg=25Ω Starting T_J = 25℃.

4.EAS condition: VDD=-15V,VGS=-10V, L=0.5mH, Rg=25Ω Starting T_J = 25℃.

5.Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.

6.Guaranteed by design, not subject to production.

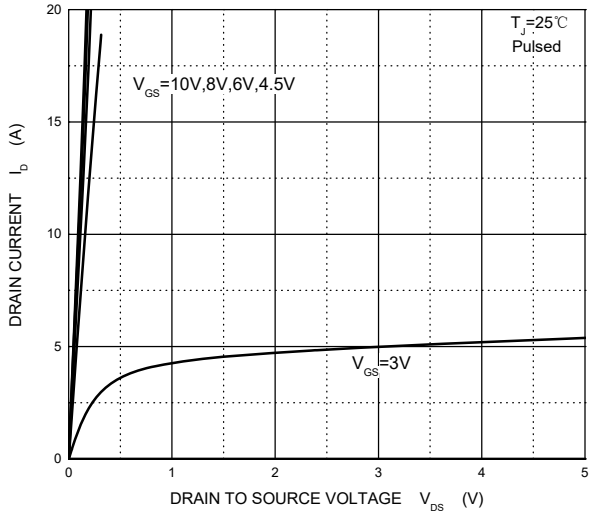
7.The value of RθJA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25℃.t ≤10sec.

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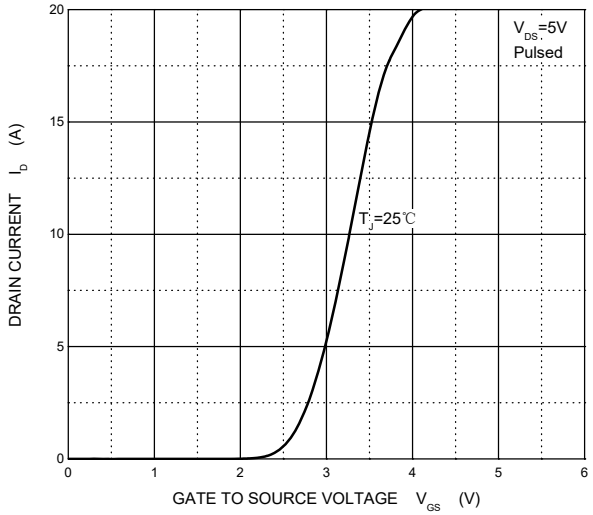
Typical Electrical and Thermal Characteristics

N-Channel MOS

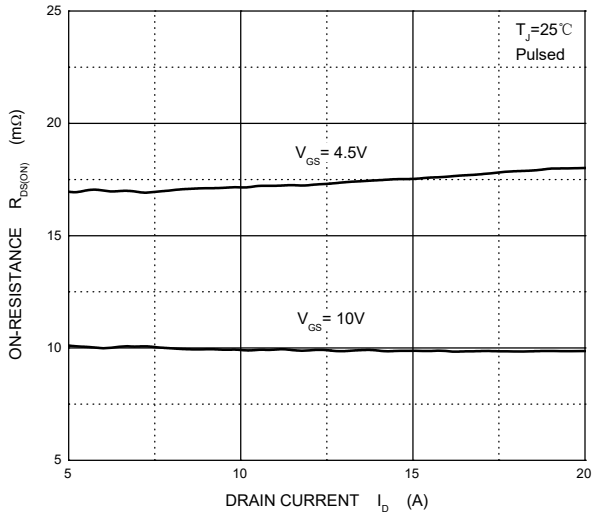
Output Characteristics



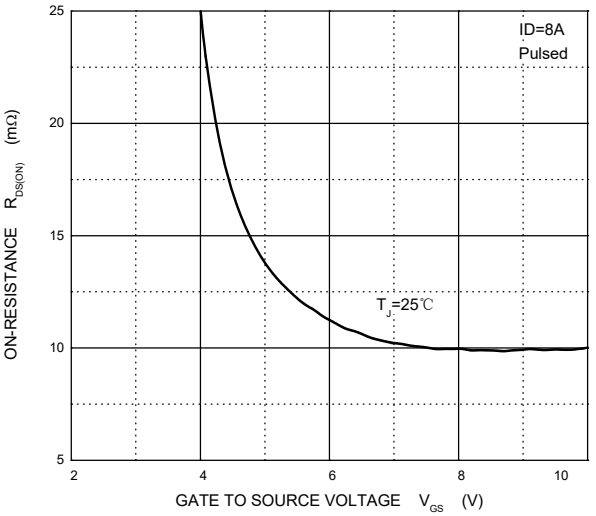
Transfer Characteristics



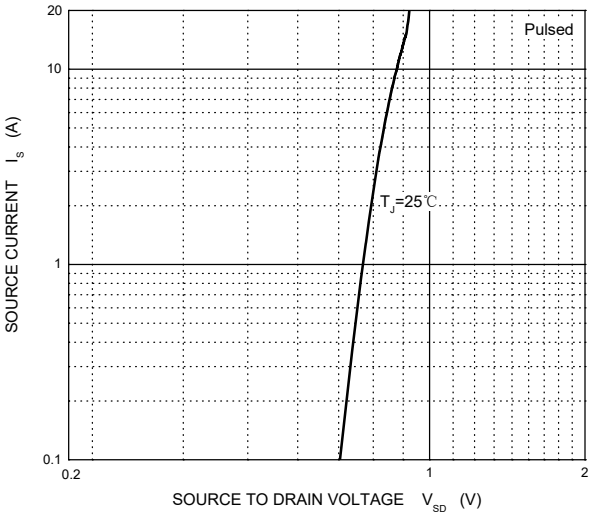
$R_{DS(ON)}$ — I_D



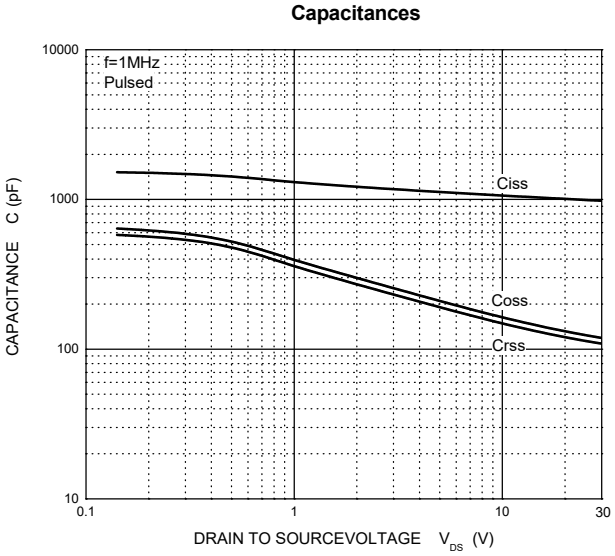
$R_{DS(ON)}$ — V_{GS}



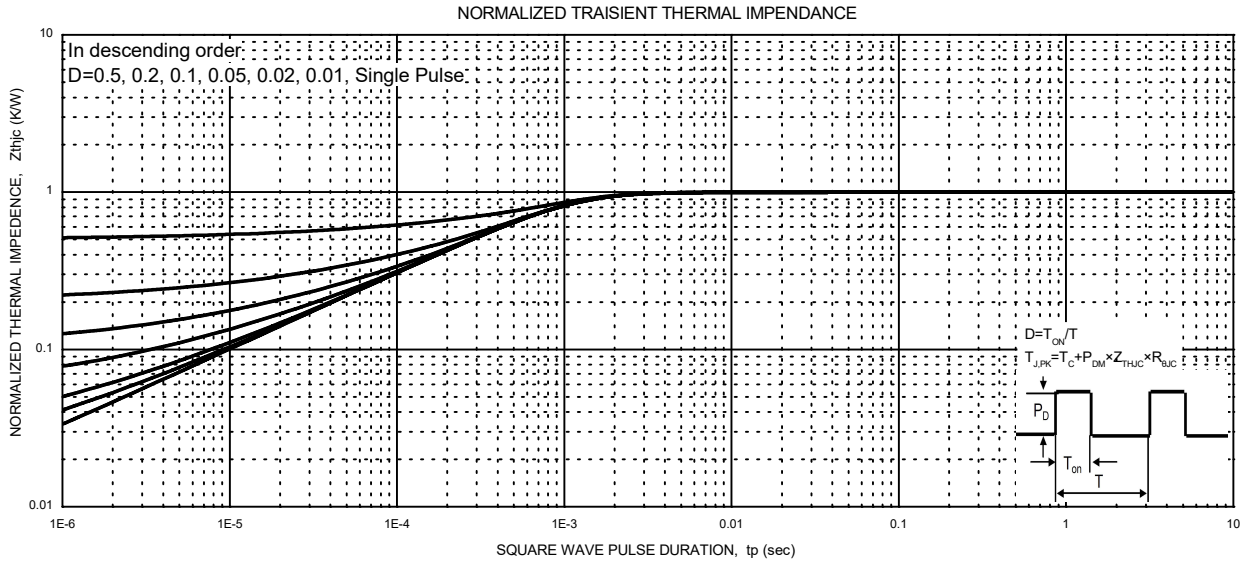
I_S — V_{SD}

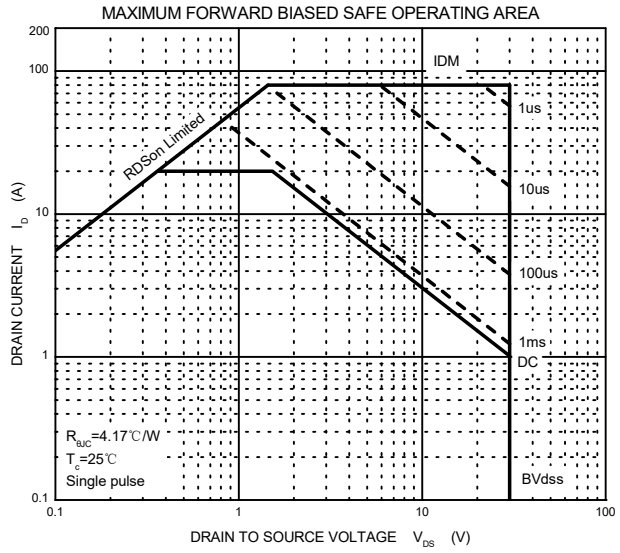


Capacitances



Typical Characteristics

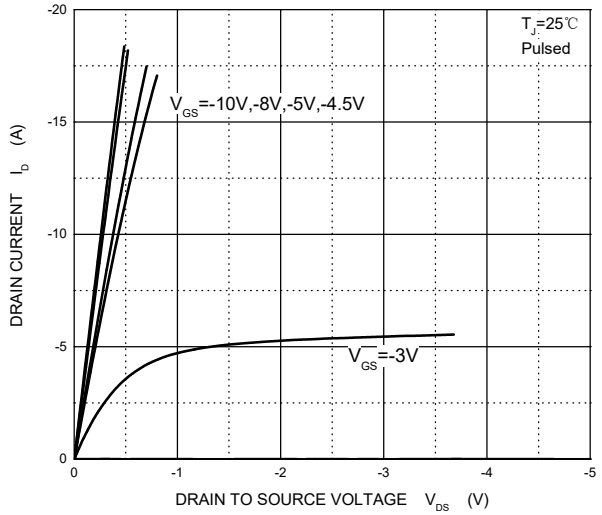




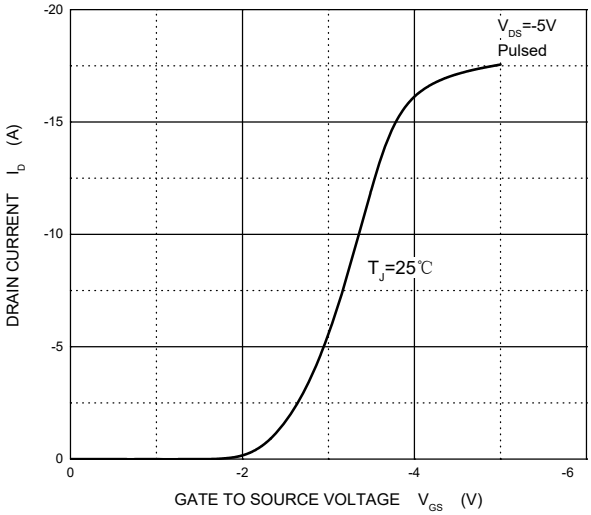
Typical Electrical and Thermal Characteristics

P-Channel MOS

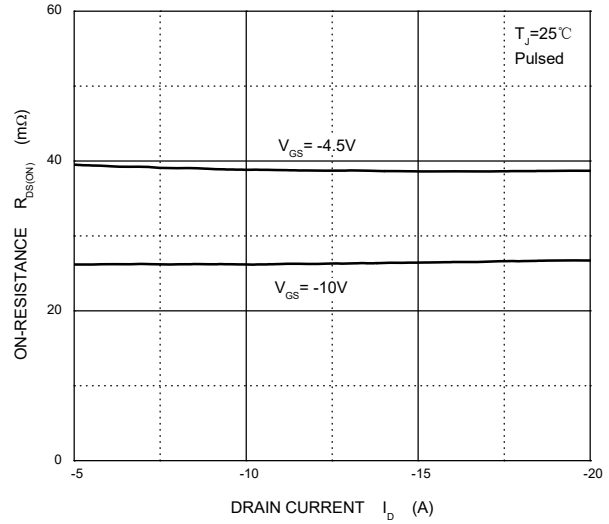
Output Characteristics



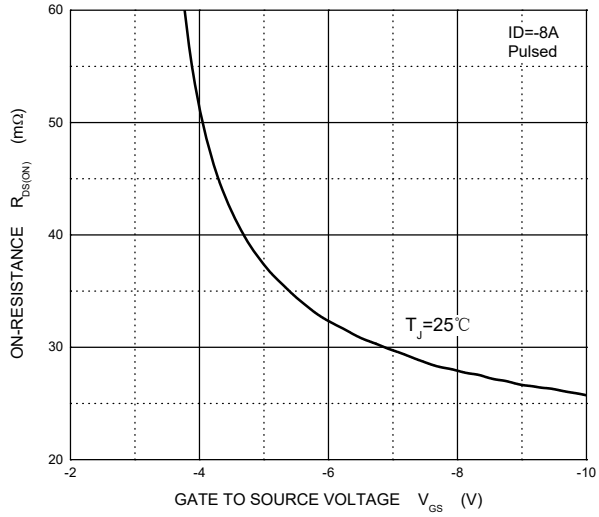
Transfer Characteristics



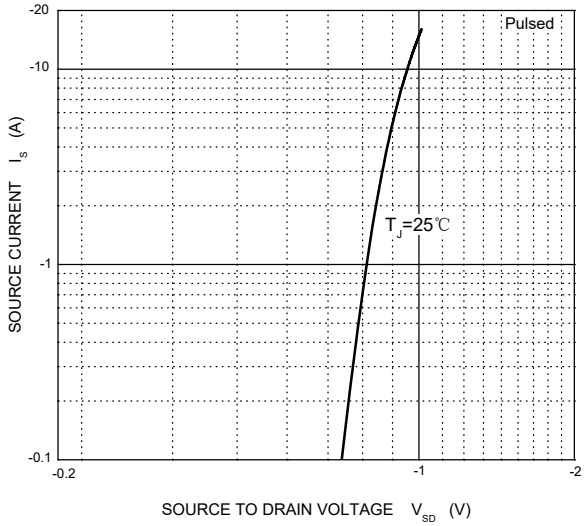
$R_{DS(ON)}$ — I_D



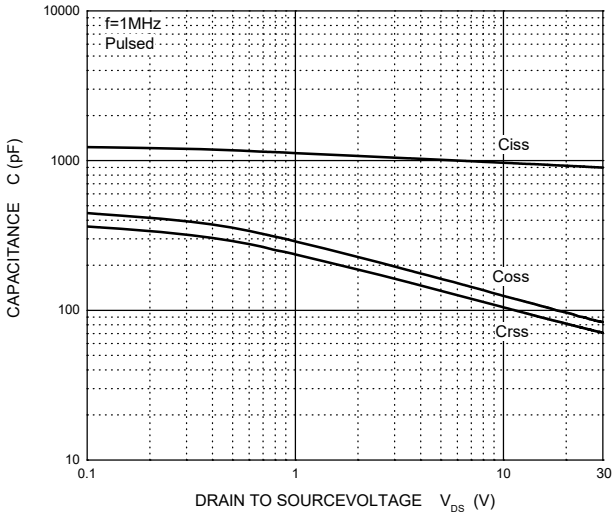
$R_{DS(ON)}$ — V_{GS}



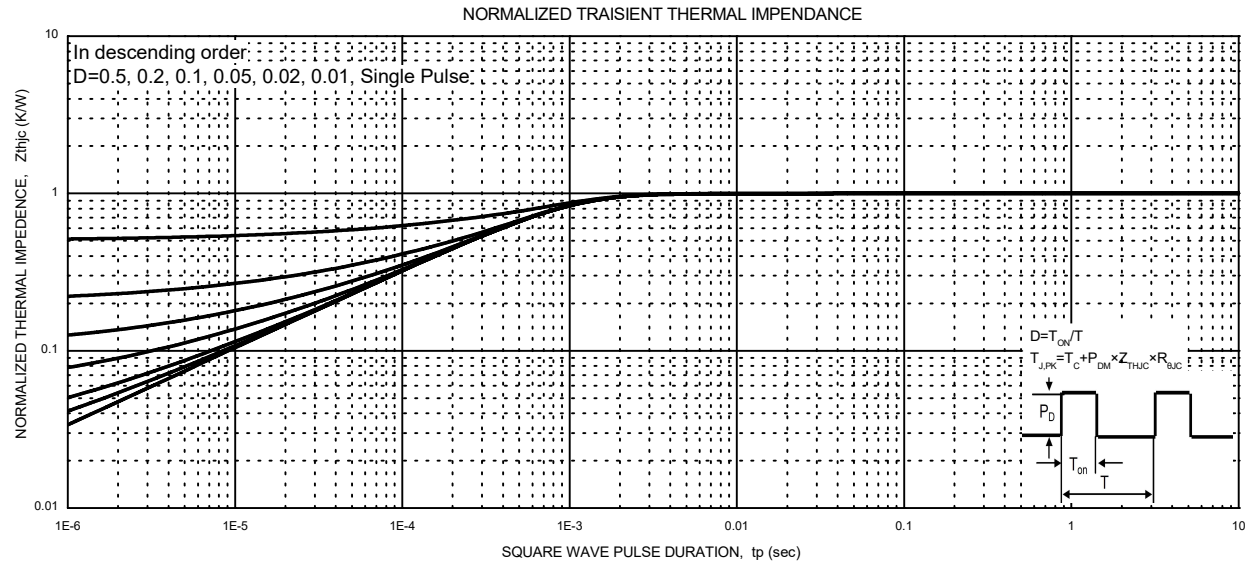
I_S — V_{SD}

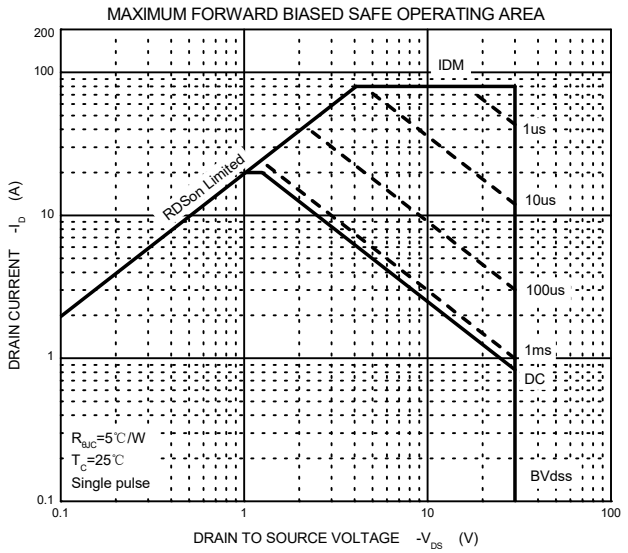


Capacitances

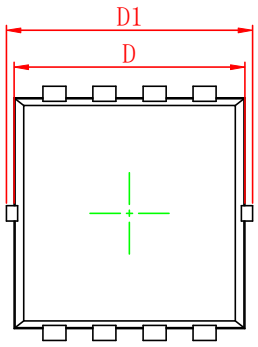


Typical Characteristics

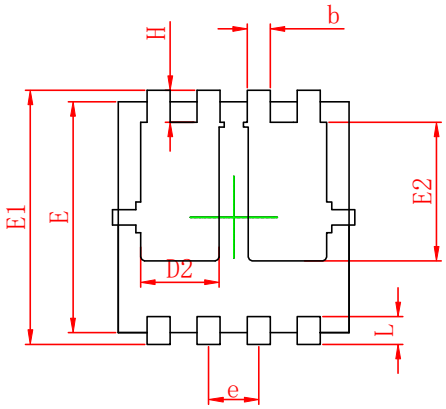




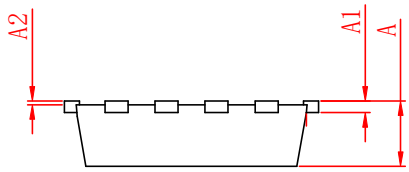
PDFNWB3.3×3.3-8L-B PACKAGE OUTLINE DIMENSIONS



Top View
[顶视图]



Bottom View
[背视图]

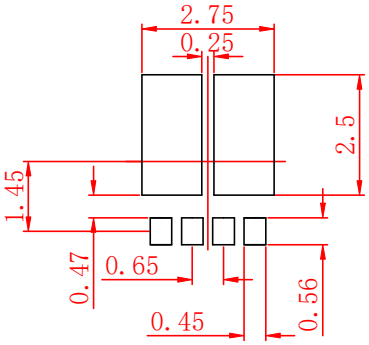


Side View
[侧视图]

Symbol	Dimensions In MillimetersDimensions In Inches			
	Min.	Max.	Min.	Max.
A	0.65	0.90	0.026	0.035
A1	0.15 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.90	3.20	0.114	0.126
D1	3.00	3.40	0.118	0.134
D2	0.90	1.15	0.035	0.045
E	2.90	3.20	0.114	0.126
E1	3.00	3.40	0.118	0.134
E2	1.60	1.90	0.063	0.075
b	0.20	0.40	0.008	0.016
e	0.65 BSC.		0.026 BSC.	
L	0.20	0.50	0.008	0.020
H	0.32	0.52	0.012	0.020

Notes：
1 Dimensions exclusive of mold gate burrs.
2 Dimensions exclusive of mold flash and cutting burrs.

PDFNWB3.3×3.3-8L-B Suggested Pad Layout

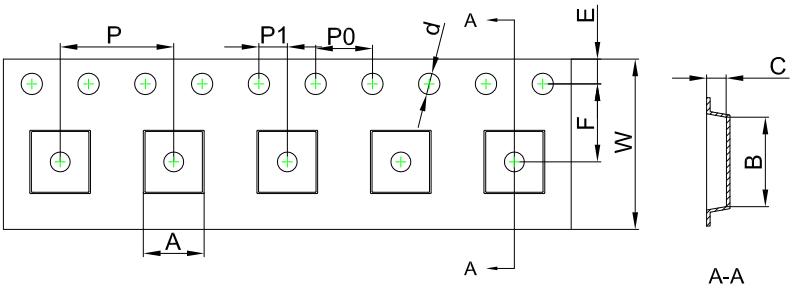


Notes：
1 Controlling dimension：in millimeters.
2 General tolerance:±0.05mm.
2 The pad layout is for referance purpose only.

NOTICE

SZCJ reservesthe right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein.SZCJ does not assume any liability arising out of the application or use of any product described herein.

PDFNWB3.3×3.3-8L-B Embossed Carrier Tape

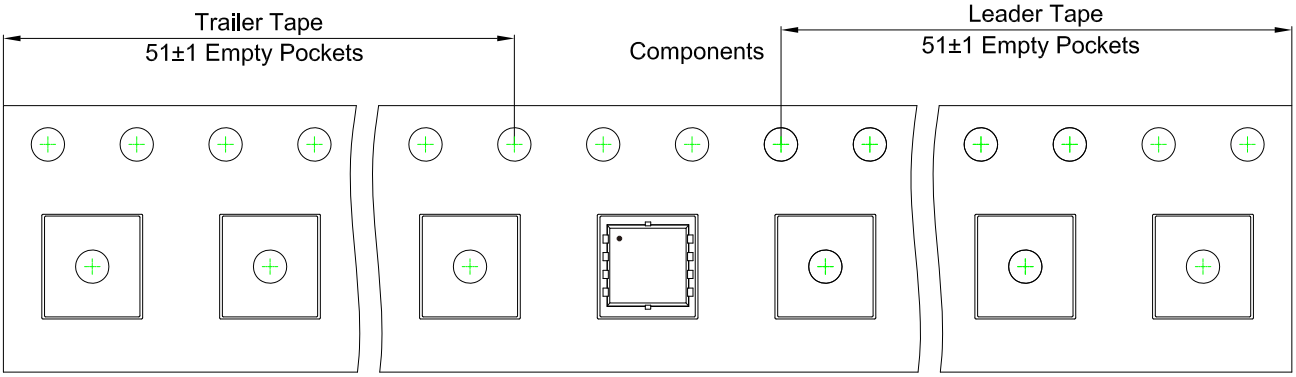


Packaging Description:

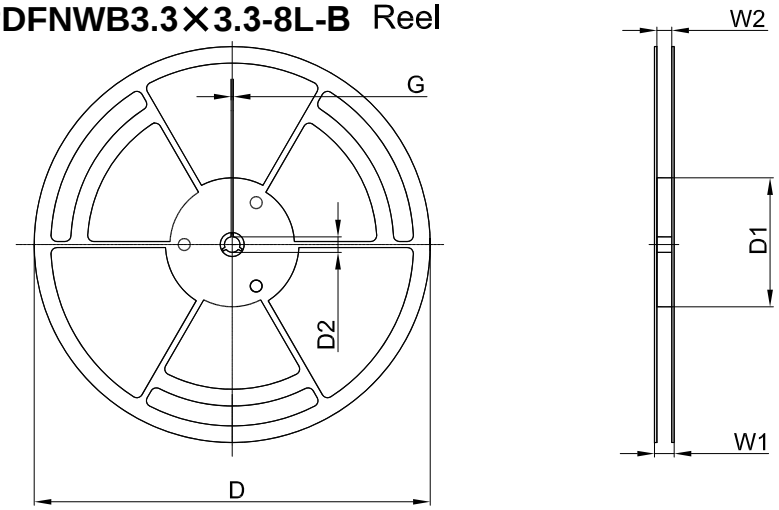
PDFNWB3.3×3.3-8L-B parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFNWB3.3×3.3-8L-B	3.55	3.55	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFNWB3.3×3.3-8L-B Tape Leader and Trailer



PDFNWB3.3×3.3-8L-B Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	10,000 pcs	340×336×29	50,000 pcs	353×346×365